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Metrology of Mo/Si multilayer mirrors at 13.5 nm with the use of a laser-produced plasma extreme ultraviolet (EUV) source based on a gas puff target

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Keywords

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Abstract

In this paper an application of a recently developed laser plasma source of extreme ultraviolet (EUV) for optical measurements of optical characteristics of Mo/Si multilayer mirrors is presented. The source is based on an xenon-helium double-stream gas puff target irradiated with laser pulses from a Nd : YAG laser system ($E = 0.55$ J, $t = 3.9$ ns, $f = 10$ Hz, $M^2 = 2.5$). The results show that the source can be useful for EUV lithography technologies as a metrology tool in the semiconductor industry.



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